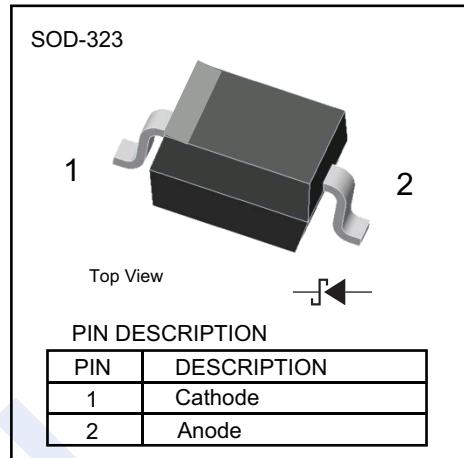


Schottky Diodes**BAT760****■ Features**

- Very Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- High Conductance

**■ Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)**

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V _{RRM}	30	V
Working Peak Reverse Voltage	V _{RWM}		
DC Blocking Voltage	V _R		
RMS Reverse Voltage	V _{R(RMS)}	21	A
Average Rectified Output Current	I _O	1	
Forward Current t = 8.3 ms Half Sinewave	I _{FSM}	5.5	mW
Power Dissipation	P _D	235	
Thermal Resistance Junction to Ambient (Note 1)	R _{θJA}	426	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

Note 1: Part mounted on FR-4 PC board with recommended pad layout

■ Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage (Note 2)	V _R	I _R = 500 μA	30			V
Forward voltage	V _{F1}	I _F = 10 mA			0.27	
	V _{F2}	I _F = 100 mA			0.35	
	V _{F3}	I _F = 1 A			0.55	
Leakage current (Note 2)	I _{R1}	V _R =5 V			10	μA
	I _{R2}	V _R =8 V			20	
	I _{R3}	V _R =15 V			50	
Total Capacitance	C _T	V _R = 5 V, f= 1 MHz		25		pF

Note 2: Short duration pulse test used to minimize self-heating effect.

Schottky Diodes

BAT760

■ Typical Characteristics

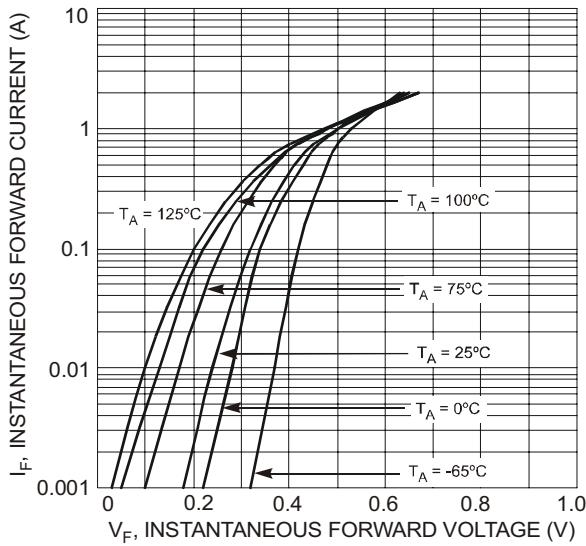


Fig. 1 Typical Forward Characteristics

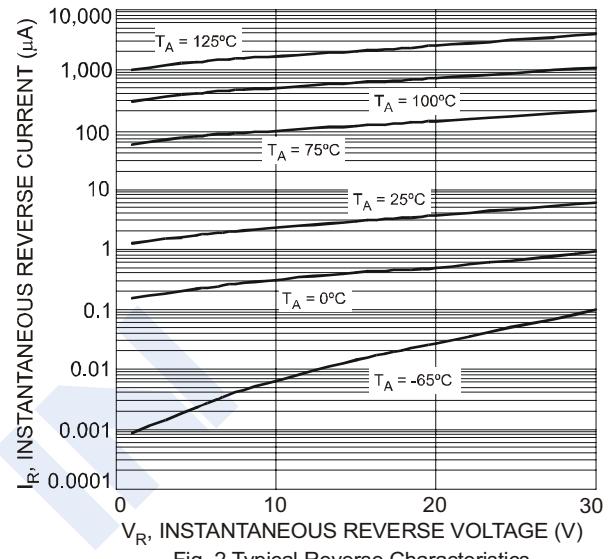


Fig. 2 Typical Reverse Characteristics

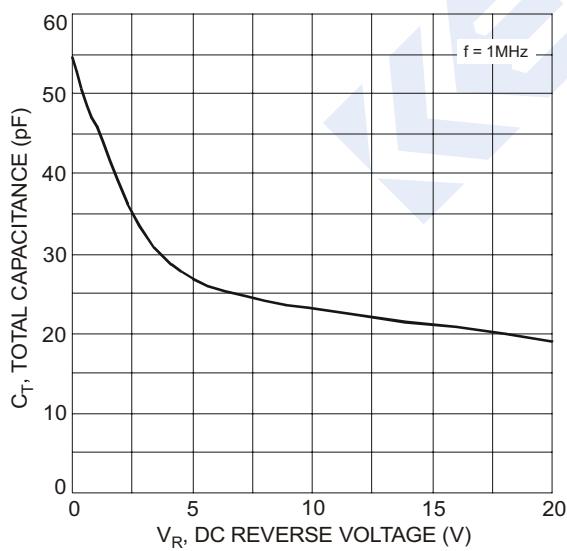


Fig. 3 Total Capacitance vs. Reverse Voltage

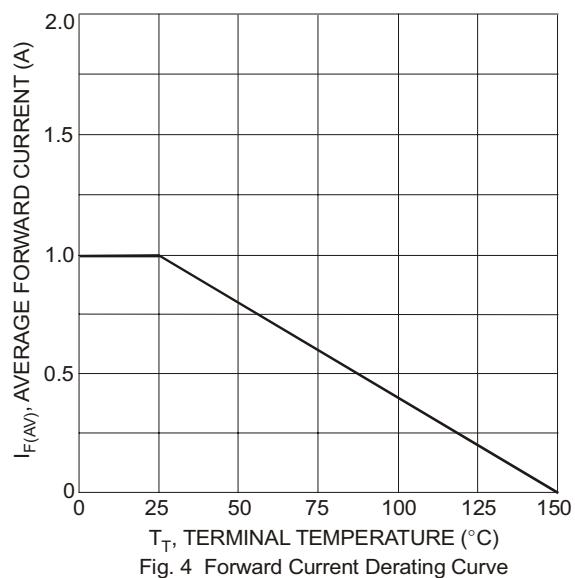
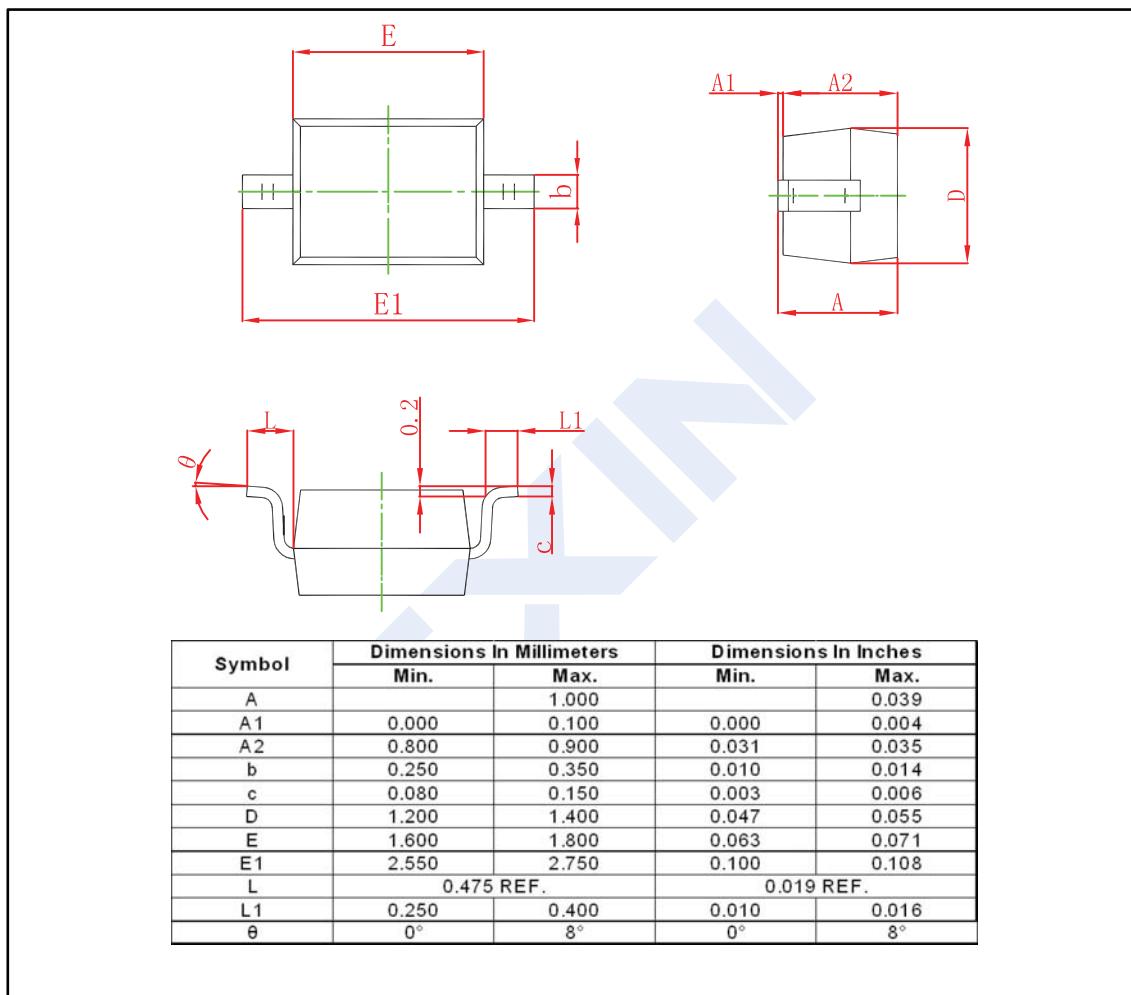
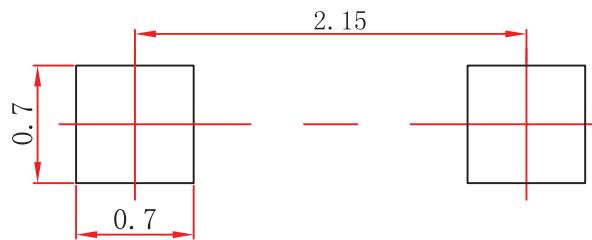


Fig. 4 Forward Current Derating Curve

Schottky Diodes**BAT760****■ Package Outline Dimensions**

Plastic surface mounted package; 2 leads

SOD-323

**■ The Recommended Mounting Pad Size****Note:**

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.